

MBRS140

SCHOTTKY BARRIER RECTIFIER

Schottky Power Rectifier Surface Mount Power Package

Employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes, in surface mount applications where compact size and weight are critical to the system.

FEATURES :

- * Very Low Forward Voltage Drop
- * Small Compact Surface Mountable Package
- * Highly Stable Oxide Passivated Junction
- * Guardring for Stress Protection
- * Pb / RoHS Free

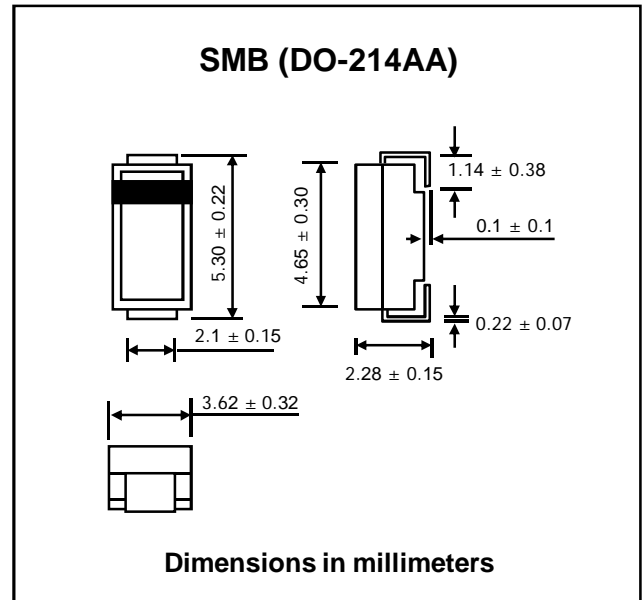
MECHANICAL DATA :

- * Case : SMB Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Lead Formed for Surface Mount
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.1079 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	VALUE	UNIT
Maximum Repetitive Reverse Voltage	VRRM	40	V
Maximum Working Peak Reverse Voltage	VRWM	40	V
Maximum DC Blocking Voltage	VDC	40	V
Maximum Average Rectified Forward Current (TL = 115°C)	IF(AV)	1.0	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions half wave, single phase)	IFSM	40	A
Maximum Instantaneous Forward Voltage (Note 1) (IF = 1.0 A, TJ = 25°C)	VF	0.60	V
Maximum Instantaneous Reverse Current (Note1) TJ = 25°C TJ = 100°C	IR	1.0	mA
		10	mA
Thermal Resistance - Junction to Lead (TL = 25°C)	RθJL	12	°C/W
Operating Junction Temperature	TJ	- 65 to +125	°C



RATING AND CHARACTERISTIC CURVES (MBR5140)

FIG.1 - CURRENT DERATING (CASE)

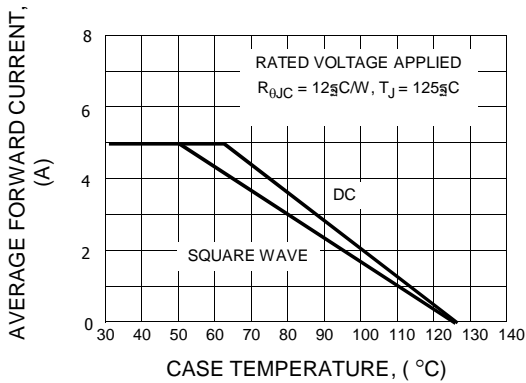


FIG.2 - POWER DISSIPATION

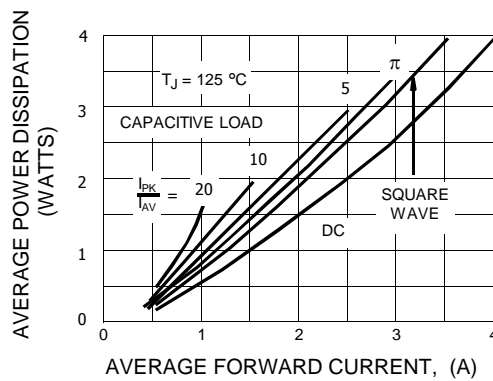


FIG.3 - TYPICAL FORWARD VOLTAGE

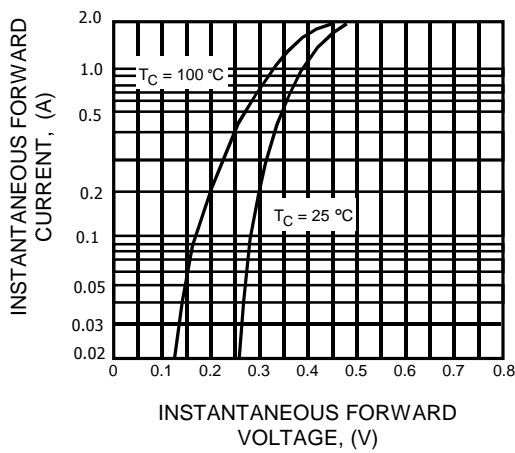


FIG.4 - TYPICAL REVERSE CURRENT

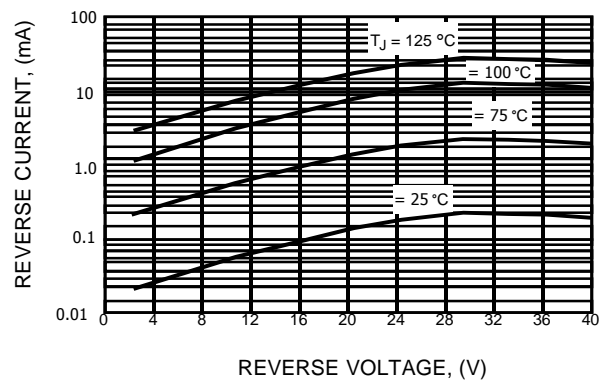


FIG. 5 TYPICAL CAPACITANCE

